

NTLJF3118N

Power MOSFET and Schottky Diode

20 V, 4.6 A, μ Cool™ N-Channel, with 2.0 A Schottky Barrier Diode, 2x2 mm WDFN Package



ON Semiconductor®

<http://onsemi.com>

Features

- WDFN 2x2 mm Package Provides Exposed Drain Pad for Excellent Thermal Conduction
- Footprint Same as SC-88 Package
- 1.8 V V_{GS} Rated $R_{DS(on)}$
- Low Profile (< 0.8 mm) for Easy Fit in Thin Environments
- Low V_F 2 A Schottky Diode
- This is a Pb-Free Device

Applications

- DC-DC Boost/Buck Converter
- Low Voltage Hard Disk DC Power Source

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	20	V	
Gate-to-Source Voltage		V_{GS}	± 12	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_D	3.8	A
				$T_A = 85^\circ\text{C}$	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$		4.6	
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	1.5	W
				$t \leq 5$ s	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	I_D	2.6	A
		$T_A = 85^\circ\text{C}$		1.9	
Power Dissipation (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	P_D	0.7	
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	18	A	
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$	
Source Current (Body Diode)		I_S	1.8	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

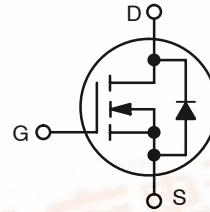
1. Surface Mounted on FR4 Board using 2 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface Mounted on FR4 Board using the minimum recommended pad size.

MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ Max	I_D Max
20 V	65 m Ω @ 4.5 V	3.8 A
	75 m Ω @ 2.5 V	2.0 A
	120 m Ω @ 1.8 V	1.7 A

SCHOTTKY DIODE

V_R Max	V_F Typ	I_F Max
20 V	0.41 V	2.0 A



N-CHANNEL MOSFET

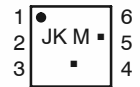


SCHOTTKY DIODE



WDFN6 CASE 506AN

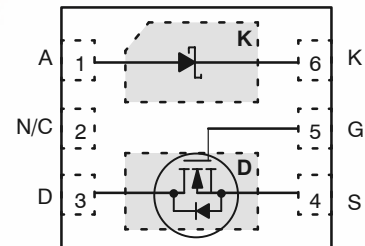
MARKING DIAGRAM



- JK = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

PIN CONNECTIONS



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.



NTLJF3118N

SCHOTTKY DIODE MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	20	V
DC Blocking Voltage	V_R	20	V
Average Rectified Forward Current	I_F	2.0	A

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	83	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	58	
Junction-to-Ambient – Steady State Min Pad (Note 4)	$R_{\theta JA}$	177	

- Surface Mounted on FR4 Board using 2 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
- Surface Mounted on FR4 Board using the minimum recommended pad size.

MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = 250$ μA	20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250$ μA , Ref to 25°C		10.4		$\text{mV}/^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16$ V, $V_{GS} = 0$ V	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 85^\circ\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 8.0$ V			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250$ μA	0.4	0.7	1.0	V
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-3.0		$\text{mV}/^\circ\text{C}$
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 4.5$ V, $I_D = 3.8$ A		37	65	m Ω
		$V_{GS} = 2.5$ V, $I_D = 2.0$ A		46	75	
		$V_{GS} = 1.8$ V, $I_D = 1.7$ A		65	120	
Forward Transconductance	g_{FS}	$V_{DS} = 10$ V, $I_D = 1.7$ A		4.2		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0$ V, $f = 1$ MHz, $V_{DS} = 10$ V		271		pF
Output Capacitance	C_{OSS}			72		
Reverse Transfer Capacitance	C_{RSS}			43		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5$ V, $V_{DS} = 10$ V, $I_D = 3.8$ A		3.7		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.3		
Gate-to-Source Charge	Q_{GS}			0.6		
Gate-to-Drain Charge	Q_{GD}			1.0		

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5$ V, $V_{DD} = 16$ V, $I_D = 1.0$ A, $R_G = 2.0$ Ω		3.8		ns
Rise Time	t_r			4.7		
Turn-Off Delay Time	$t_{d(OFF)}$			11.1		
Fall Time	t_f			5.8		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0$ V, $I_S = 1.0$ A	$T_J = 25^\circ\text{C}$		0.69	1.0	V
Reverse Recovery Time	t_{RR}	$V_{GS} = 0$ V, $dI_{SD}/dt = 100$ A/ μs , $I_S = 1.0$ A			10.2		ns

- Pulse Test: Pulse Width ≤ 300 μs , Duty Cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.

NTLJF3118N

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage	V_F	$I_F = 0.1\text{ A}$		0.26	0.35	V
		$I_F = 1.0\text{ A}$		0.35	0.42	
		$I_F = 2.0\text{ A}$		0.41	0.52	
Maximum Instantaneous Reverse Current	I_R	$V_R = 20\text{ V}$		0.20	5.0	mA
		$V_R = 10\text{ V}$		0.045	1.0	

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 85^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage	V_F	$I_F = 0.1\text{ A}$		0.18		V
		$I_F = 1.0\text{ A}$		0.29		
		$I_F = 2.0\text{ A}$		0.36		
Maximum Instantaneous Reverse Current	I_R	$V_R = 20\text{ V}$		4.9		mA
		$V_R = 10\text{ V}$		1.6		

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 125^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage	V_F	$I_F = 0.1\text{ A}$		0.13		V
		$I_F = 1.0\text{ A}$		0.25		
		$I_F = 2.0\text{ A}$		0.33		
Maximum Instantaneous Reverse Current	I_R	$V_R = 20\text{ V}$		42		mA
		$V_R = 10\text{ V}$		13		

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Capacitance	C	$V_R = 5.0\text{ V}$, $f = 1.0\text{ MHz}$		52.3		pF

ORDERING INFORMATION

Device	Package	Shipping [†]
NTLJF3118NTAG	WDFN6 (Pb-Free)	3000 / Tape & Reel
NTLJF3118NTBG	WDFN6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTLJF3118N

TYPICAL N-CHANNEL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

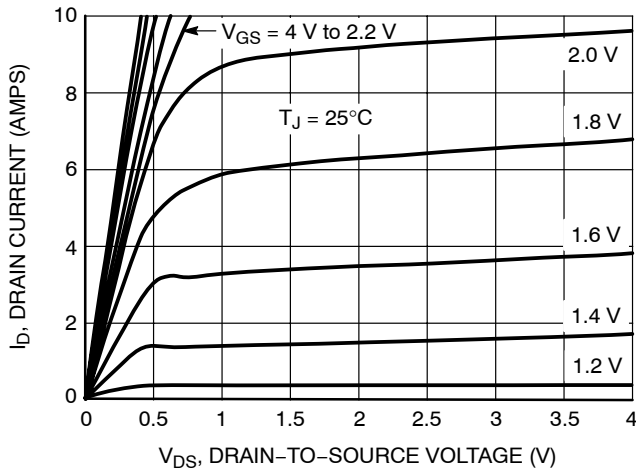


Figure 1. On-Region Characteristics

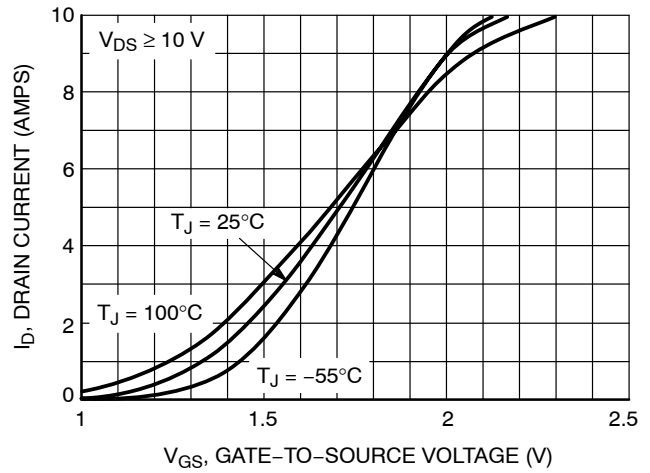


Figure 2. Transfer Characteristics

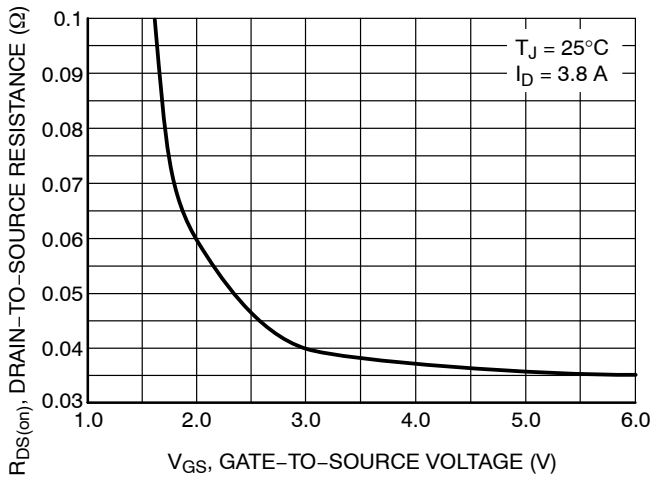


Figure 3. On-Resistance versus Drain Current

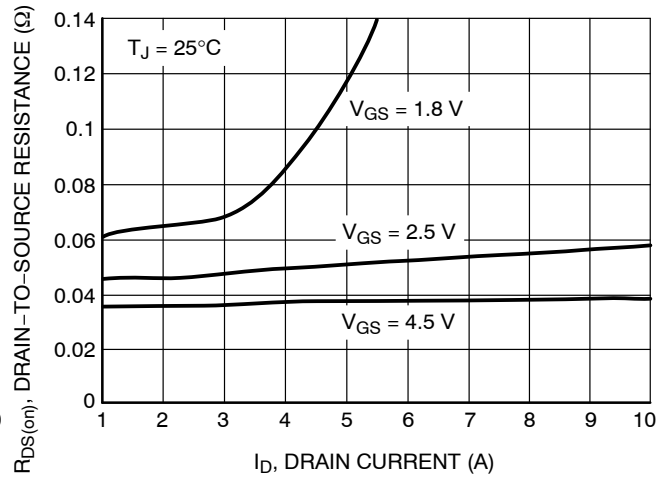


Figure 4. On-Resistance versus Drain Current and Gate Voltage

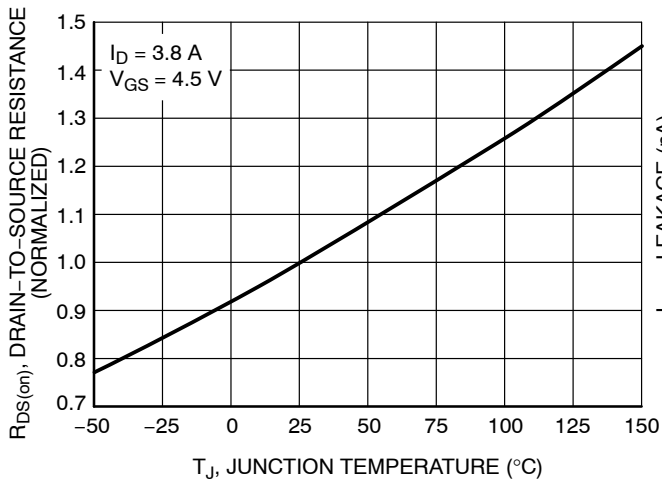


Figure 5. On-Resistance Variation with Temperature

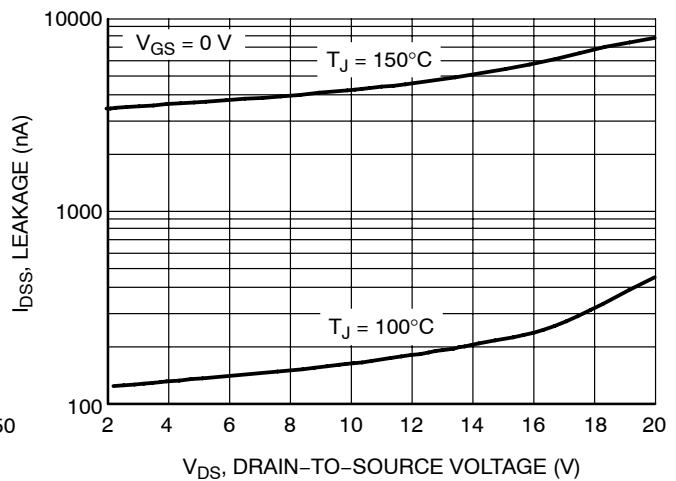


Figure 6. Drain-to-Source Leakage Current versus Voltage

NTLJF3118N

TYPICAL N-CHANNEL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

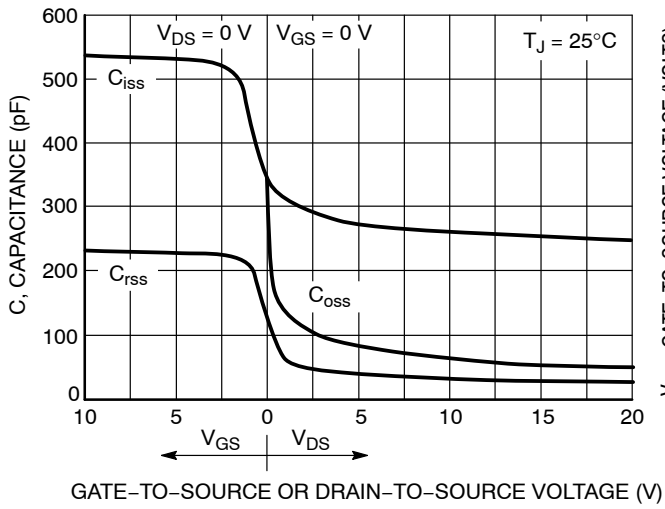


Figure 7. Capacitance Variation

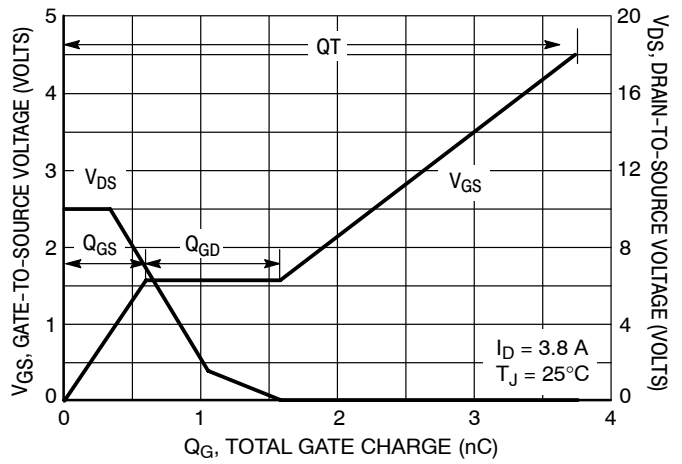


Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

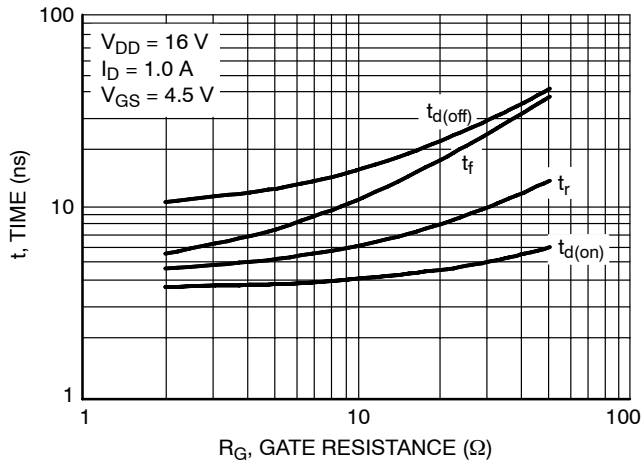


Figure 9. Resistive Switching Time Variation versus Gate Resistance

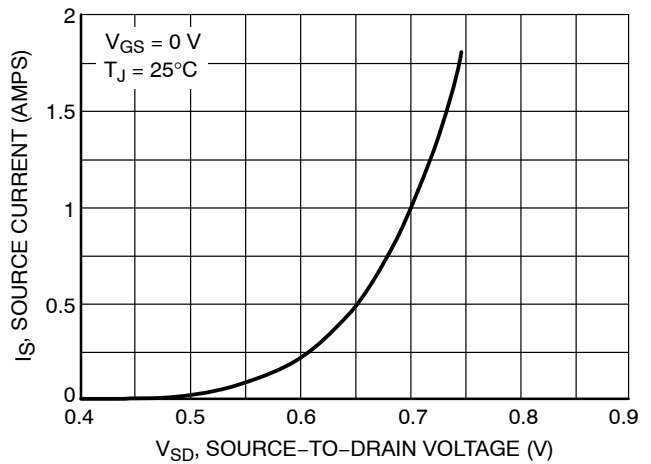


Figure 10. Diode Forward Voltage versus Current

NTLJF3118N

TYPICAL SCHOTTKY PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

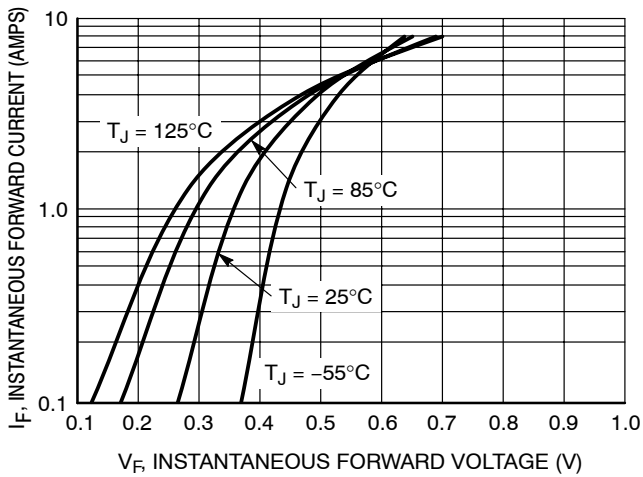


Figure 11. Typical Forward Voltage

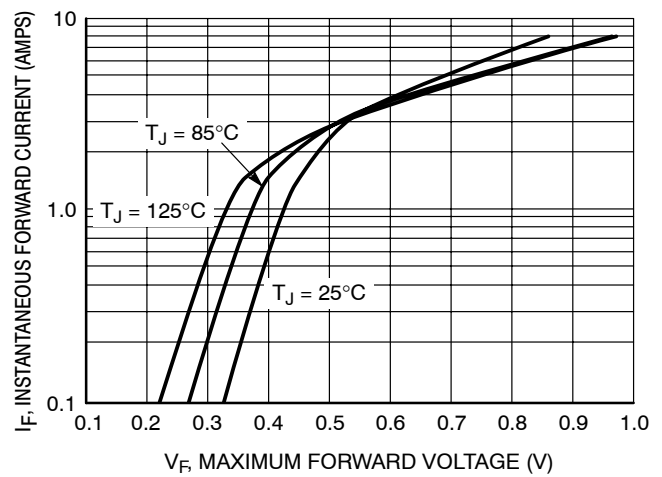


Figure 12. Maximum Forward Voltage

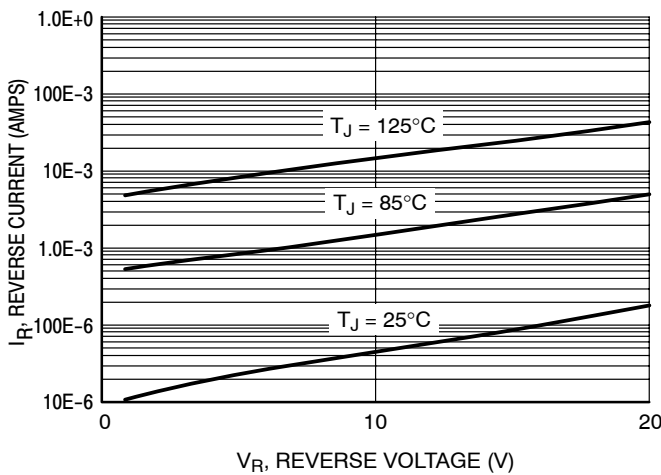


Figure 13. Typical Reverse Current

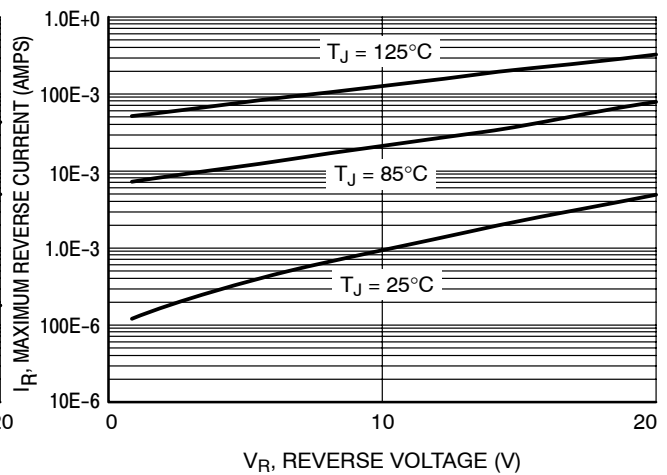
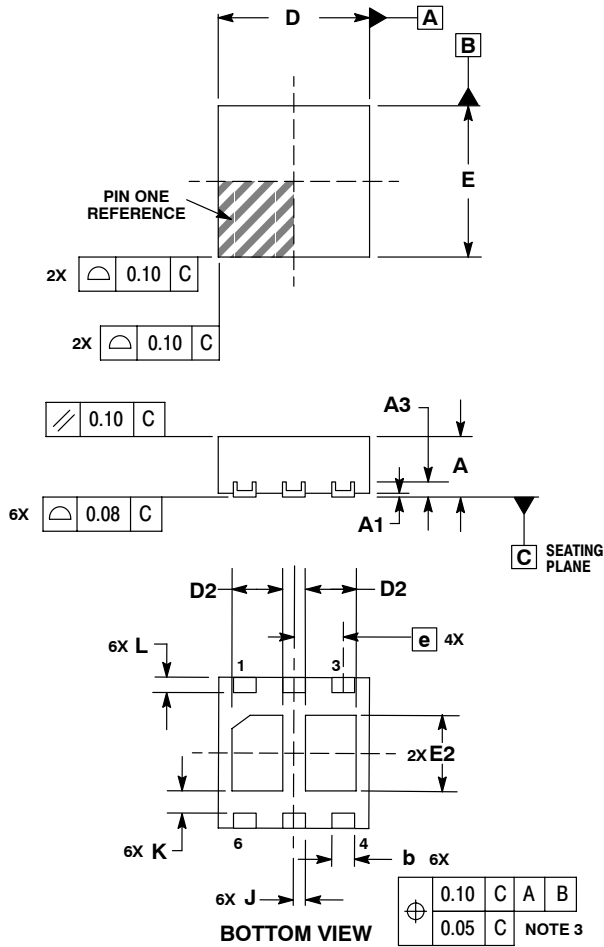


Figure 14. Maximum Reverse Current

NTLJF3118N

PACKAGE DIMENSIONS

WDFN6, 2x2
CASE 506AN-01
ISSUE B

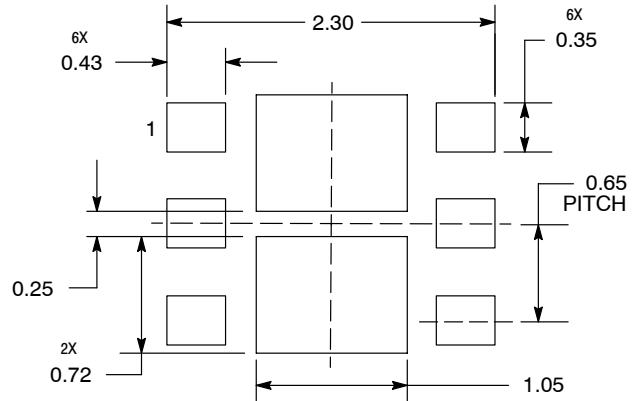


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20mm FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.70	0.80
A1	0.00	0.05
A3	0.20 REF	
b	0.25	0.35
D	2.00 BSC	
D2	0.57	0.77
E	2.00 BSC	
E2	0.90	1.10
e	0.65 BSC	
K	0.25 REF	
L	0.20	0.30
J	0.15 REF	

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

µCool is a trademark of Semiconductor Components Industries, LLC (SCILLC).

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910
Japan Customer Focus Center Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative